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[VS-ETH1506S-M3](#)

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## VS-ETH1506S-M3, VS-ETH1506-1-M3

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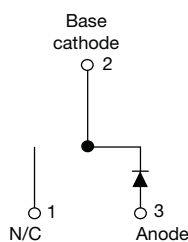
### Hyperfast Rectifier, 15 A FRED Pt<sup>®</sup>



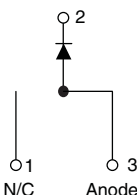
TO-263AB (D<sup>2</sup>PAK)



TO-262AA



VS-ETH1506S-M3



VS-ETH1506-1-M3

#### FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

#### DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

#### PRODUCT SUMMARY

Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA
I <sub>F(AV)</sub>	15 A
V <sub>R</sub>	600 V
V <sub>F</sub> at I <sub>F</sub>	1.25 V
t <sub>rr</sub> (typ.)	21 ns
T <sub>J</sub> max.	175 °C
Diode variation	Single die

#### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 139 °C	15	A
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	160	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

#### ELECTRICAL SPECIFICATIONS (T<sub>J</sub> = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15A	-	1.8	2.45	
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.25	1.6	
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	0.01	15	μA
		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	20	200	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	12	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH



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## VS-ETH1506S-M3, VS-ETH1506-1-M3

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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 30 V	-	21	26	ns	
		I <sub>F</sub> = 15 A, dI <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 30 V	-	25	36		
		T <sub>J</sub> = 25 °C	-	29	-		
		T <sub>J</sub> = 125 °C	-	65	-		
Peak recovery current	I <sub>RRM</sub>	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	T <sub>J</sub> = 25 °C	-	3.9	-	A
			T <sub>J</sub> = 125 °C	-	7.0	-	
Reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 800 A/μs V <sub>R</sub> = 390 V	T <sub>J</sub> = 25 °C	-	60	-	nC
			T <sub>J</sub> = 125 °C	-	240	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 800 A/μs V <sub>R</sub> = 390 V	-	42	-	ns
Peak recovery current	I <sub>RRM</sub>			-	21	-	A
Reverse recovery charge	Q <sub>rr</sub>			-	480	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.3	1.51	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	70	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D <sup>2</sup> PAK modified	ETH1506S			
		Case style TO-262	ETH1506-1			



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**VS-ETH1506S-M3, VS-ETH1506-1-M3**

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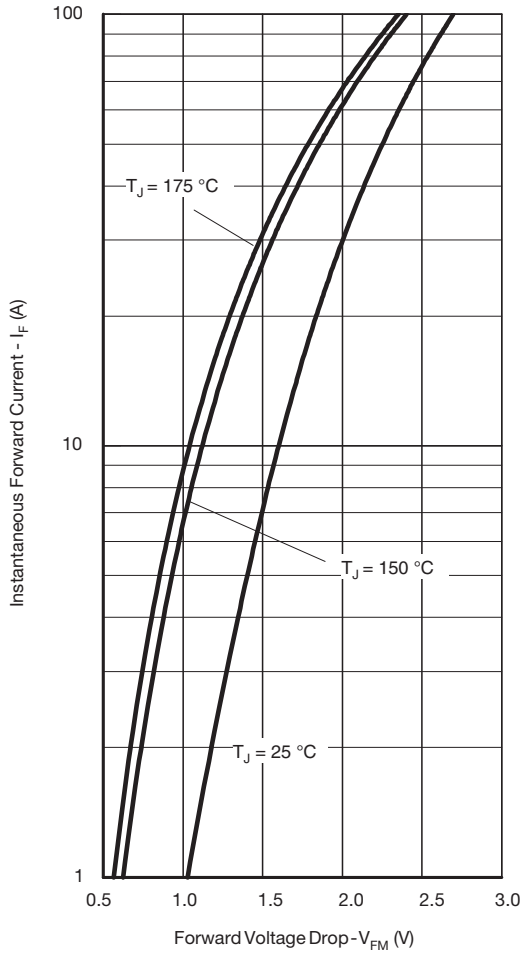


Fig. 1 - Typical Forward Voltage Drop Characteristics

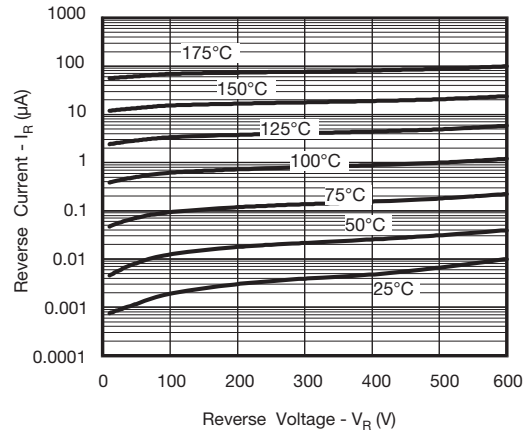


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

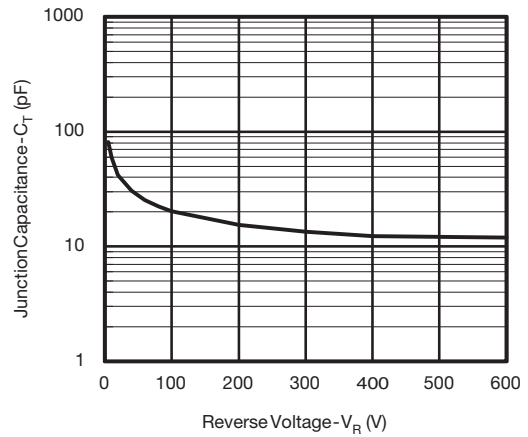


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

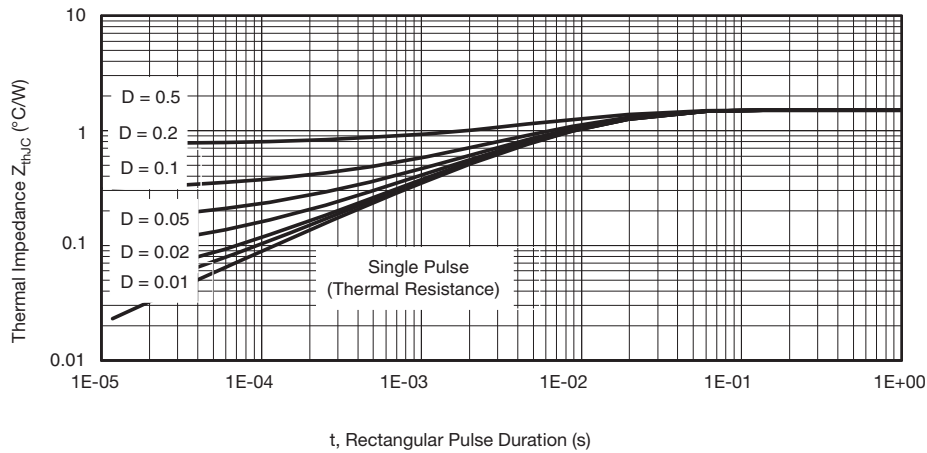


Fig. 4 - Max. Thermal Impedance  $Z_{thJC}$  Characteristics



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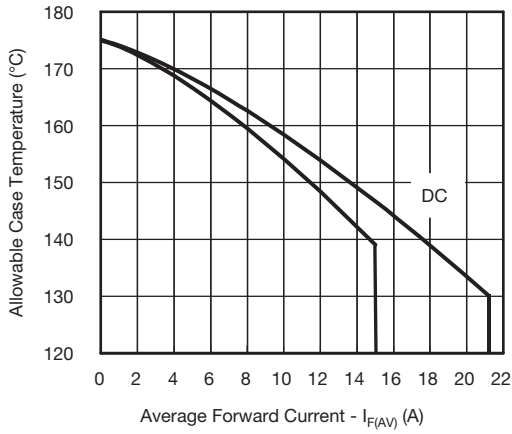


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

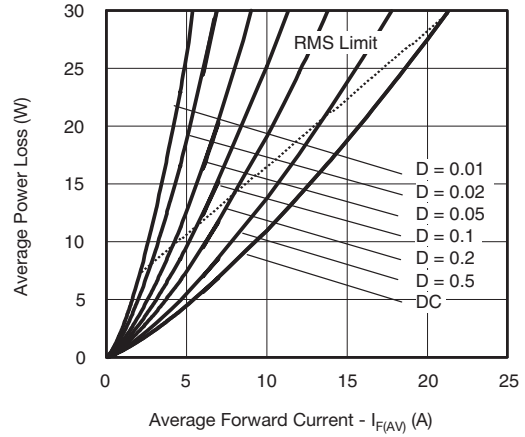


Fig. 6 - Forward Power Loss Characteristics

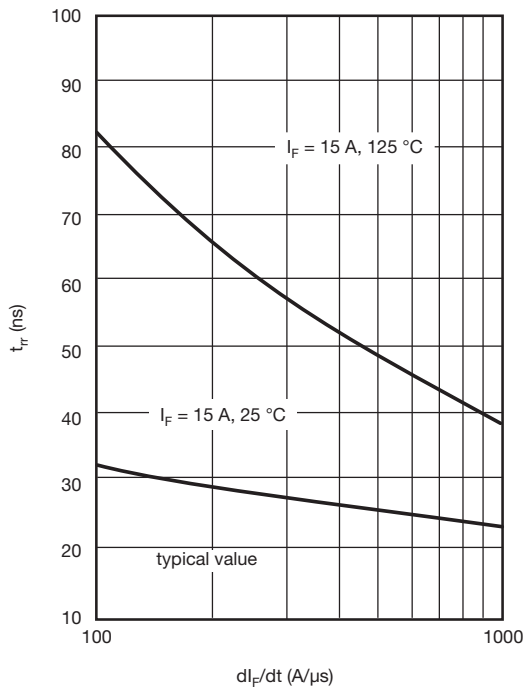


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$

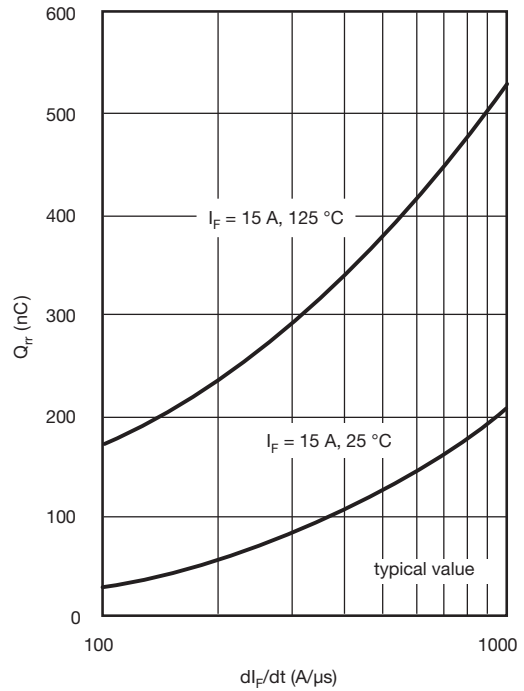


Fig. 8 - Typical Stored Charge vs.  $dI_F/dt$



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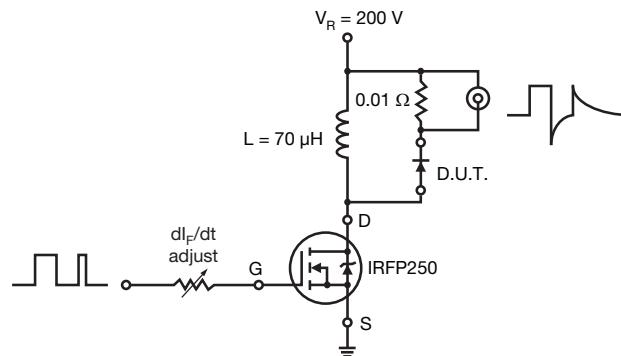
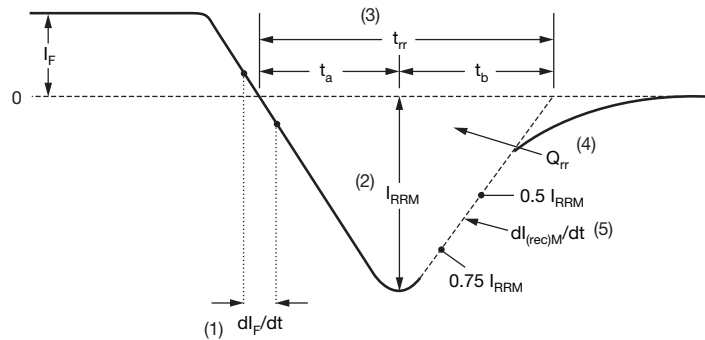


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1)  $di_F/dt$  - rate of change of current through zero crossing
- (2)  $I_{RRM}$  - peak reverse recovery current
- (3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 10 - Reverse Recovery Waveform and Definitions



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# VS-ETH1506S-M3, VS-ETH1506-1-M3

Vishay Semiconductors

## ORDERING INFORMATION TABLE

Device code	VS-	E	T	H	15	06	S	TRL	-M3
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Circuit configuration  
E = single diode
- 3** - T = TO-220
- 4** - H = hyperfast recovery time
- 5** - Current code (15 = 15 A)
- 6** - Voltage code (06 = 600 V)
- 7** - • S = D<sup>2</sup>PAK  
• -1 = TO-262
- 8** - • None = tube (50 pieces)  
• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK package)  
• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)
- 9** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-ETH1506S-M3	50	1000	Antistatic plastic tube
VS-ETH1506-1-M3	50	1000	Antistatic plastic tube
VS-ETH1506STRR-M3	800	800	13" diameter reel
VS-ETH1506STRL-M3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS		
Dimensions	TO-263AB (D <sup>2</sup> PAK)	<a href="http://www.vishay.com/doc?95046">www.vishay.com/doc?95046</a>
	TO-262AA	<a href="http://www.vishay.com/doc?95419">www.vishay.com/doc?95419</a>
Part marking information	TO-263AB (D <sup>2</sup> PAK)	<a href="http://www.vishay.com/doc?95444">www.vishay.com/doc?95444</a>
	TO-262AA	<a href="http://www.vishay.com/doc?95443">www.vishay.com/doc?95443</a>
Packaging information	TO-263AB (D <sup>2</sup> PAK)	<a href="http://www.vishay.com/doc?95032">www.vishay.com/doc?95032</a>



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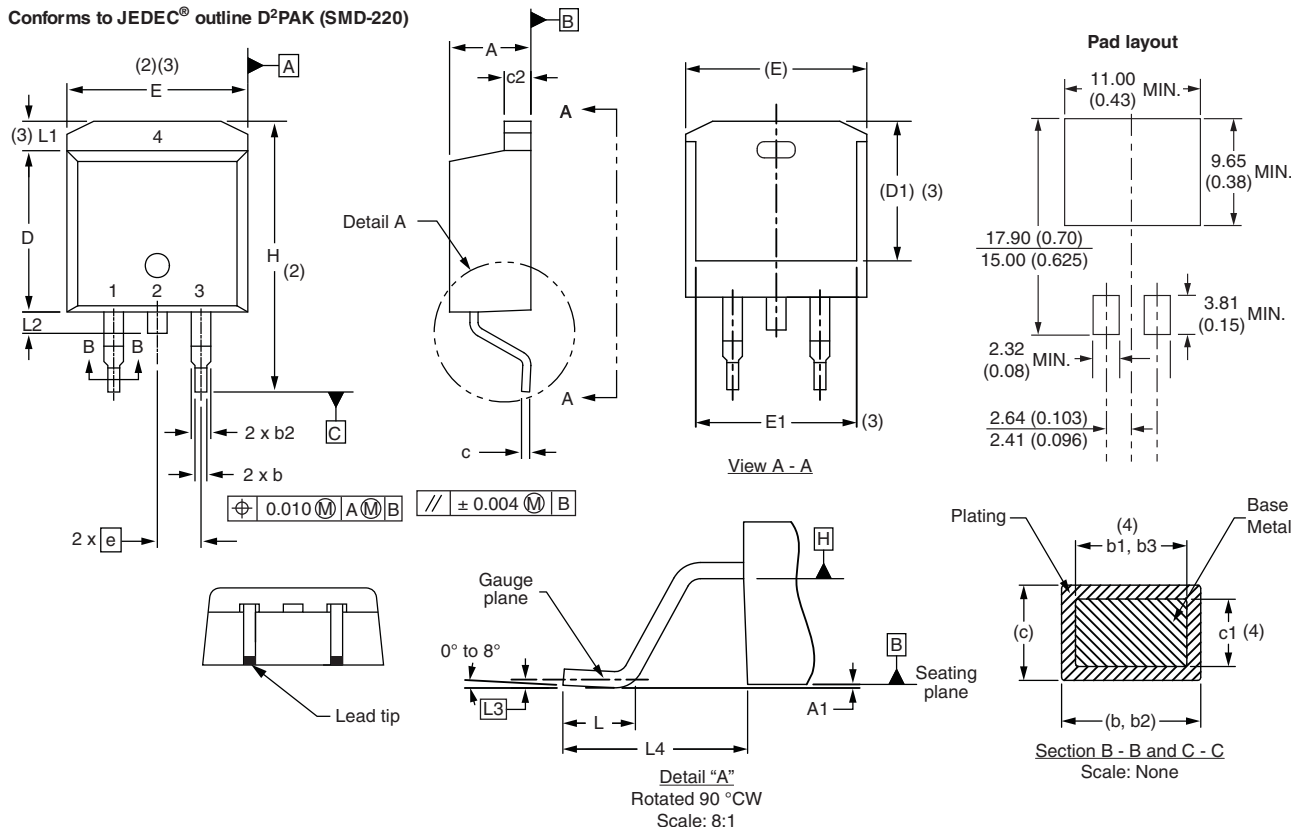
# Outline Dimensions

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## D<sup>2</sup>PAK

**DIMENSIONS** in millimeters and inches

Conforms to JEDEC<sup>®</sup> outline D<sup>2</sup>PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

**Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC<sup>®</sup> outline TO-263AB





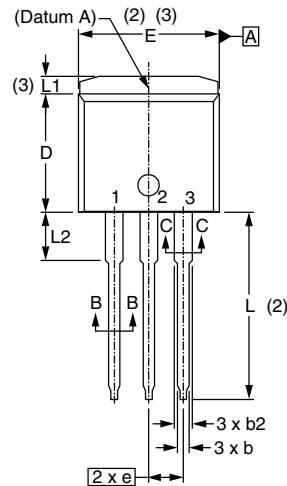
# Outline Dimensions

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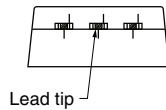
## TO-262

**DIMENSIONS** in millimeters and inches

Modified JEDEC outline TO-262

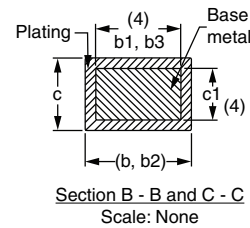
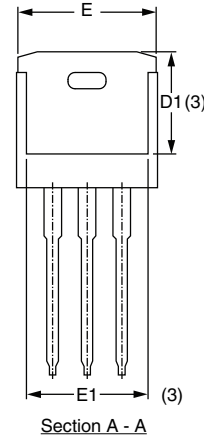
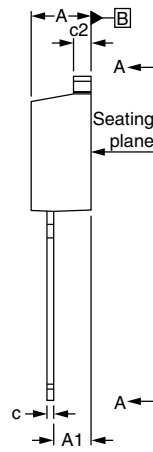


$\oplus 0.010 \text{ (M) (A) (M) (B)}$



**Lead assignments**

- Diodes  
 1. - Anode (two die)/open (one die)  
 2., 4. - Cathode  
 3. - Anode



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

**Notes**

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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